

## ABSTRACT OF THE DISCLOSURE

A word current source (445) for a magnetoresistive random access memory circuit (420) includes an n-channel transistor (430) including a gate, a source and a drain, where the source is coupled to a supply ground, and the drain is coupled to the magnetoresistive  
5 random access memory circuit. A positive supply voltage is coupled to the magnetoresistive random access memory circuit (420) so as to allow current to flow through the magnetoresistive random access memory circuit (420) when an activation signal is applied to the gate by the control circuit.

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